# **Monolithic Amplifier**

## DC-1 GHz

#### **Product Features**

- Wideband, DC to 1 GHz
- Cascadable ceramic package
- Low noise figure, 3.0 dB typ.
- Excellent repeatability
- · Aqueous washable



**RAM-8+** 

CASE STYLE: AF190-1 PRICE: \$4.60 ea. QTY. (30)

+ RoHS compliant in accordance with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

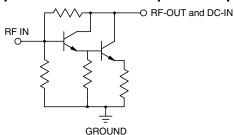
## **Typical Applications**

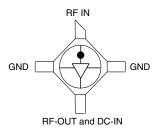
- Cellular
- UHF/VHF
- Communication system
- Transmition receivers

## **General Description**

RAM-8+ (RoHS compliant) is a wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in a ceramic surface-mount package. RAM-8+ uses Darlington configuration and is fabricated using silicon technology. Expected MTBF is 200 years at 100°C case temperature.

#### simplified schematic and pin description





Function	Pin Number	Description	
RF IN	1	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
RF-OUT and DC-IN	3	RF output and bias pin. DC voltage is present on this pin; therefore a DC blocking capacitor is necessary for proper operation. An RF choke is needed to feed DC bias without loss of RF signal due to the bias connection, as shown in "Recommended Application Circuit".	
GND	2,4	Connections to ground. Use via holes as shown in "Suggested Layout for PCB Design" to reduce ground path inductance for best performance.	





**RAM-8+** 

## Electrical Specifications at 25°C and 36mA, unless noted

Parameter		Min.	Тур.	Max.	Units
Frequency Range*		DC		1	GHz
Gain	f=0.1 GHz		32.5		dB
	f=1 GHz	19²	23		
Input Return Loss					
				lances are not 50	
Output Return Loss		see S-parameter data. Conditionally stable, source and load VSWR< 3:1 required.			
Output Power @ 1 dB compression	f=1 GHz		12.5		dBm
Output IP3	f=1 GHz		+27		dBm
Noise Figure	f=1 GHz		3		dB
Recommended Device Operating Current			36		mA
Device Operating Voltage		7.8		V	
Thermal Resistance, junction-to-case <sup>1</sup>			175		°C/W

<sup>\*</sup>Guaranteed specification DC-1 GHz. Low frequency cut off determined by external coupling capacitors.

## **Absolute Maximum Ratings**

Parameter	Ratings		
Operating Temperature	-54°C to 100°C		
Storage Temperature	-65°C to 150°C		
Operating Current	65mA		
Power Dissipation	420mW		
Input Power	13dBm		

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation. 

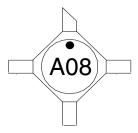
¹Case is defined as ground leads. 
²Full temperature range.





Monolithic Amplifier RAM-8+

### **Product Marking**



#### **Additional Detailed Technical Information**

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: AF190-1

Ceramic surface-mount, .083 body diameter, lead finish: tin plate

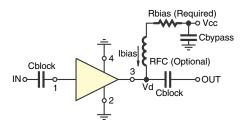
Tape & Reel: F14

Suggested Layout for PCB Design: PL-254

Evaluation Board: TB-414-8+

**Environmental Ratings: ENV08T6** 

## **Recommended Application Circuit**



Test Board includes case, connectors, and components (in bold) soldered to  $\ensuremath{\mathsf{PCB}}$ 

R BIAS				
Vcc	"1%" Res. Values (ohms) for Optimum Biasing			
10	63.4			
11	90.9			
12	115			
13	143			
14	169			
15	200			





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## **ESD Rating**

Human Body Model (HBM): Class 0 (< 250 v) in accordance with ANSI/ESD STM 5.1 - 2001 Charged Device Model (CDM): Class III ( < 500 to 1000 v) in accordance with JESD22-C101C



